

Product Summary

Device	V _{(BR)DSS}	R _{DS(ON)} max	I _D MAX T _A = +25°C
N-Channel	30V	20mΩ @ V _{GS} = 10V	7.3A
		24mΩ @ V _{GS} = 4.5V	6.7A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC Motor Control
- DC-AC Inverters

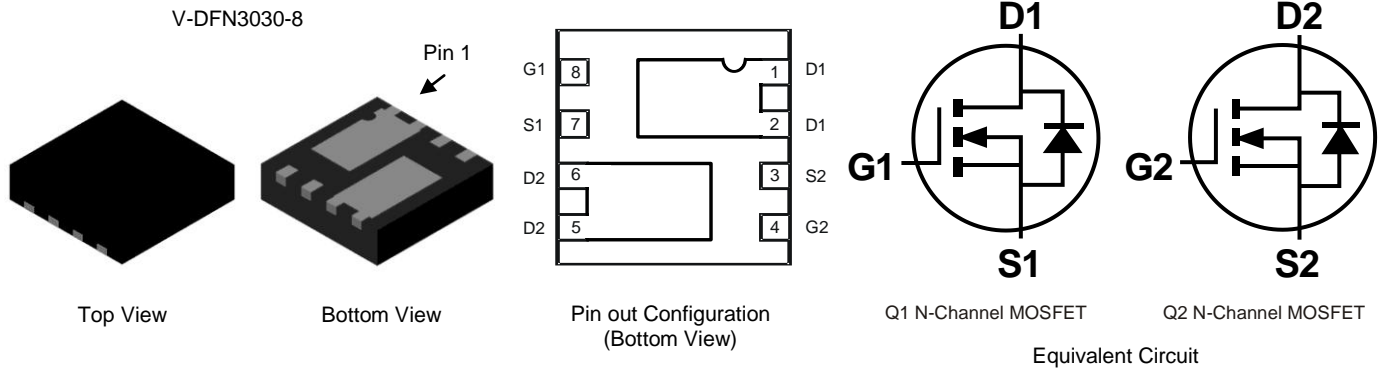
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: V-DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.02 grams (Approximate)

NEW PRODUCT

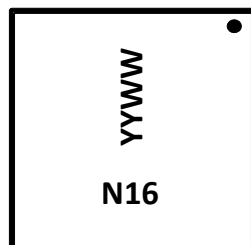


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LDN-7	V-DFN3030-8	3000/Tape & Reel
DMN3016LDN-13	V-DFN3030-8	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N16 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 13 for 2013)
 WW = Week Code (01 ~ 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	7.3 5.8	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	9.2 7.3	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	45	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	22	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	24	mJ

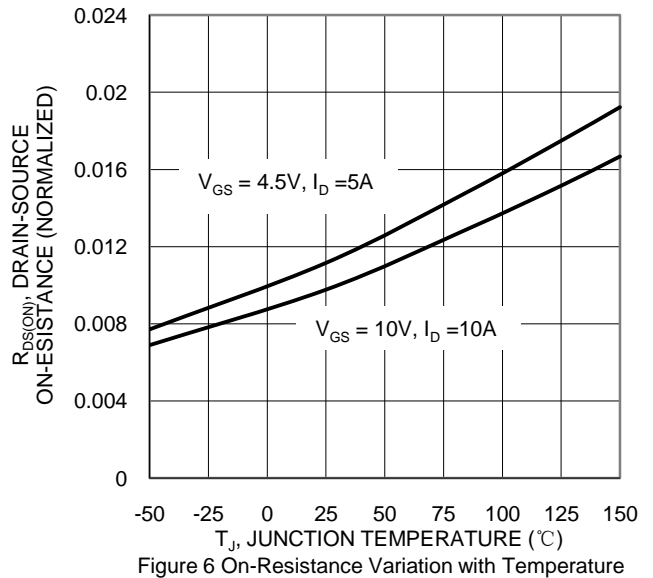
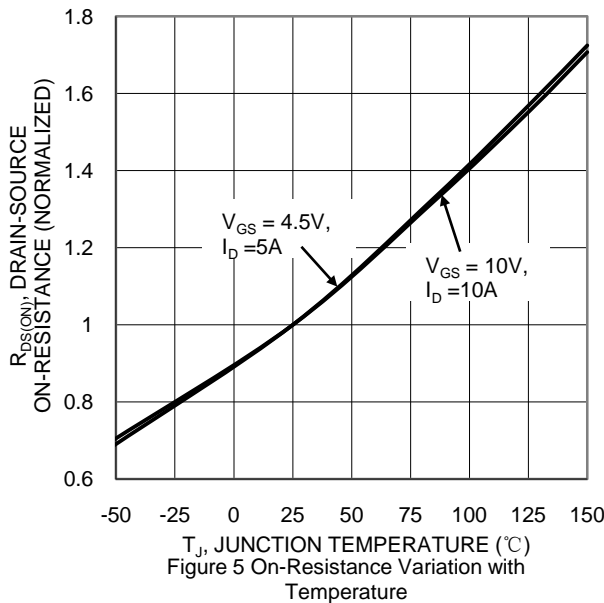
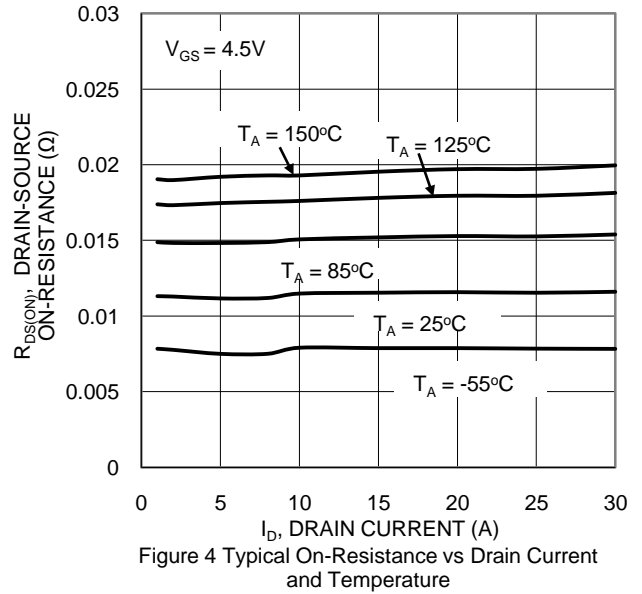
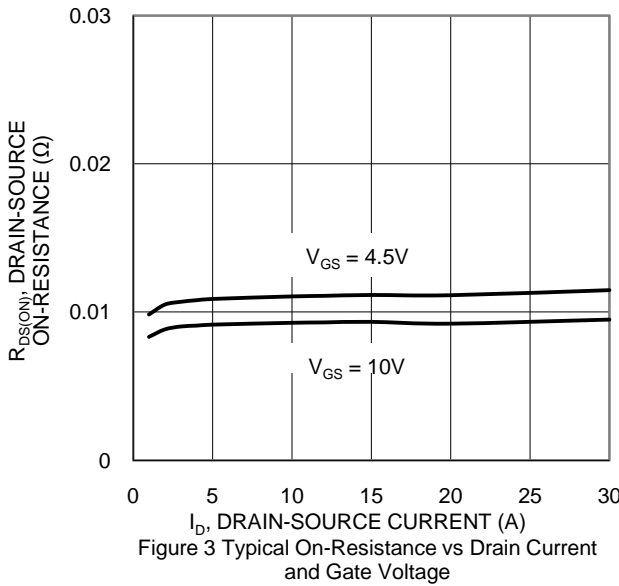
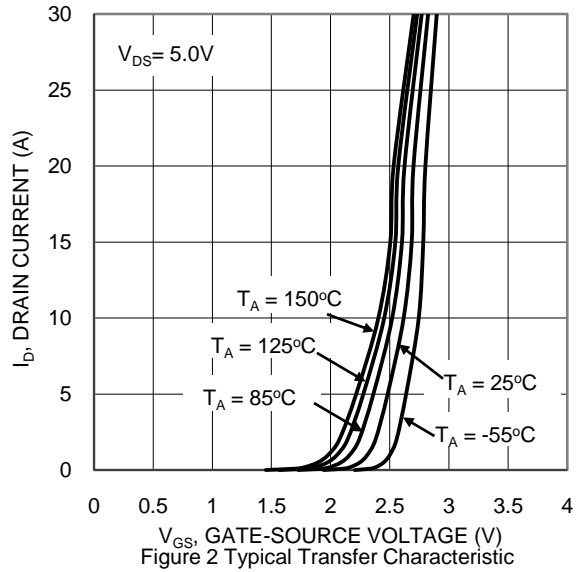
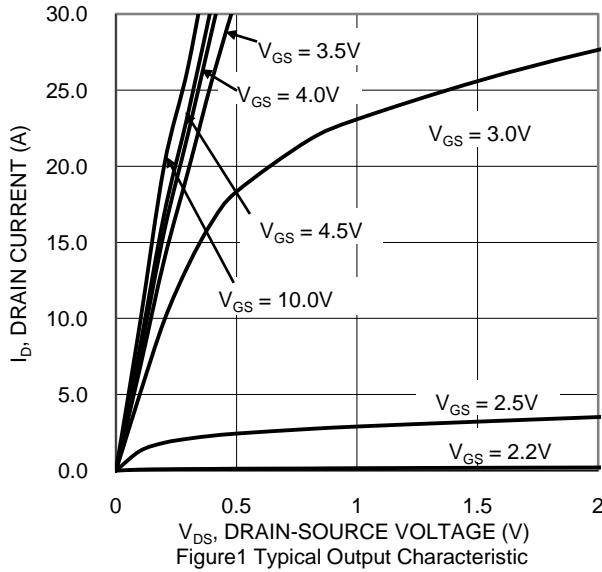
Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	119	°C/W
	t < 10s		75	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	78	°C/W
	t < 10s		49	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	13.5	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	µA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.4	-	2.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	20	mΩ	V _{GS} = 10V, I _D = 11A
		-	-	24		V _{GS} = 4.5V, I _D = 9A
Diode Forward Voltage	V _{SD}	-	0.70	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	1415	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	119	-		
Reverse Transfer Capacitance	C _{rss}	-	82	-		
Gate Resistance	R _g	-	2.6	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	11.3	-	nC	V _{DS} = 15V, I _D = 12A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	25.1	-		
Gate-Source Charge	Q _{gs}	-	3.5	-		
Gate-Drain Charge	Q _{gd}	-	3.6	-		
Turn-On Delay Time	t _{D(ON)}	-	4.8	-	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 1.25Ω, R _G = 3Ω
Turn-On Rise Time	t _R	-	16.5	-		
Turn-Off Delay Time	t _{D(OFF)}	-	26.1	-		
Turn-Off Fall Time	t _F	-	5.6	-		
Reverse Recovery Time	t _{RR}	-	12.3	-	ns	I _F = 12A, di/dt = 500A/µs
Reverse Recovery Charge	Q _{rr}	-	10.4	-	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1in. square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



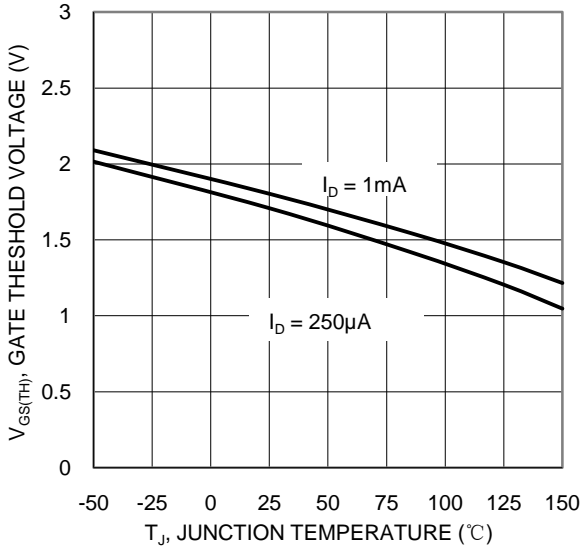


Figure 7 Gate Threshold Variation vs Junction Temperature

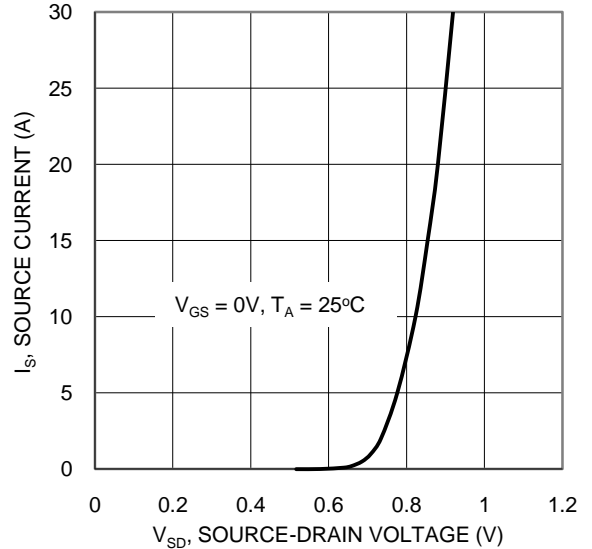


Figure 8 Diode Forward Voltage vs Current

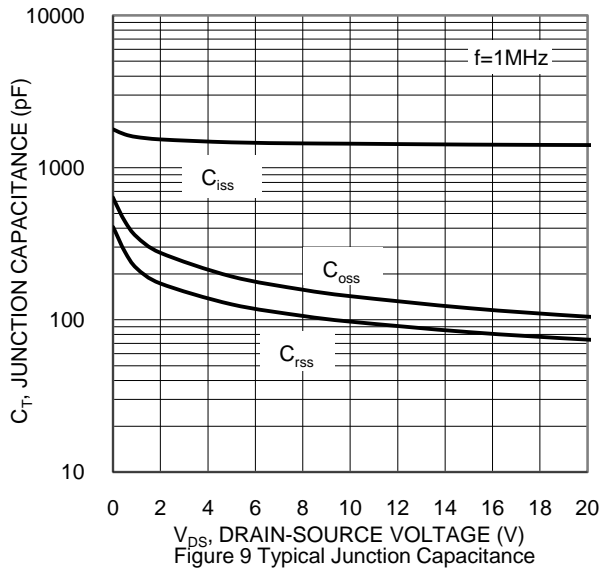


Figure 9 Typical Junction Capacitance

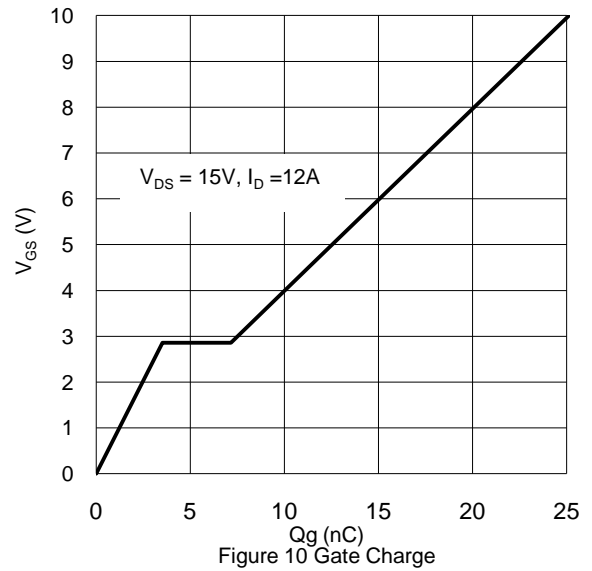


Figure 10 Gate Charge

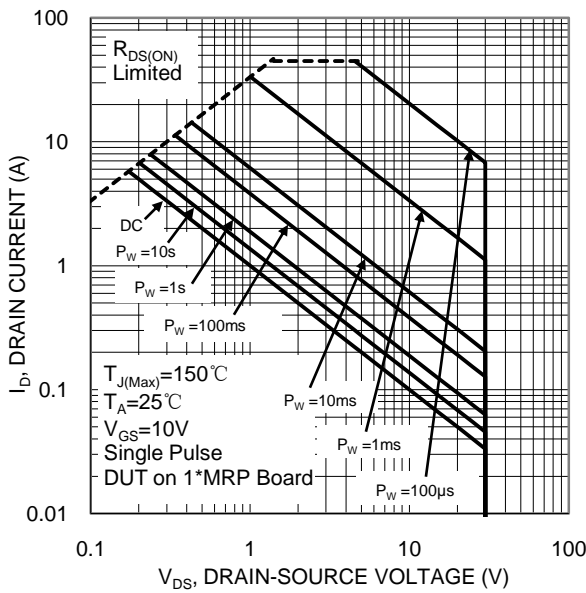


Figure 11 SOA, Safe Operation Area

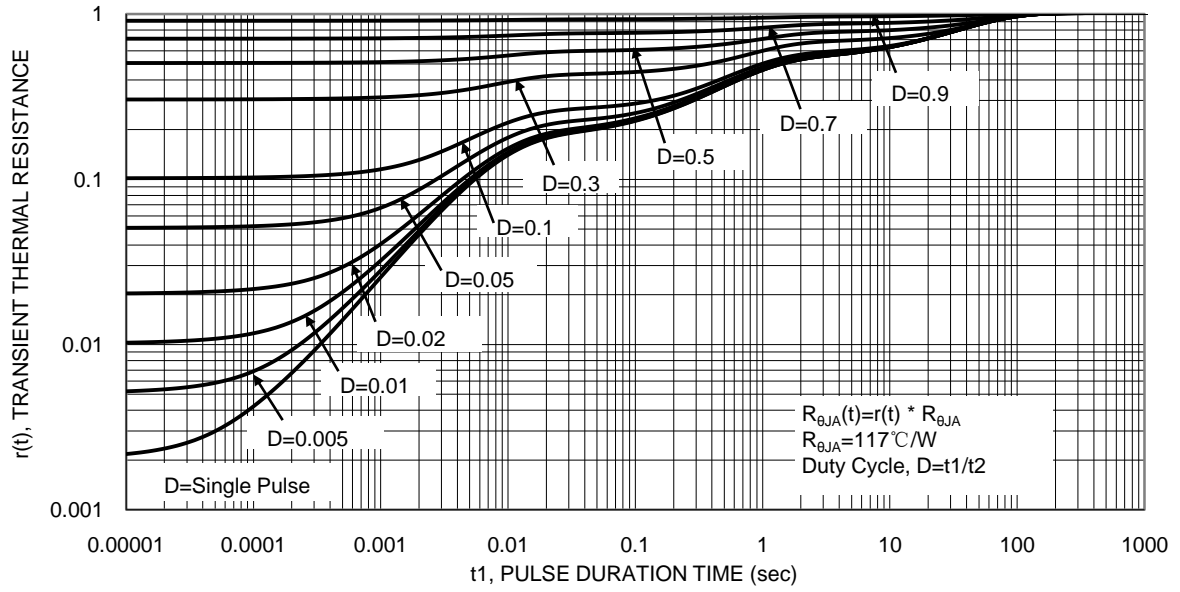
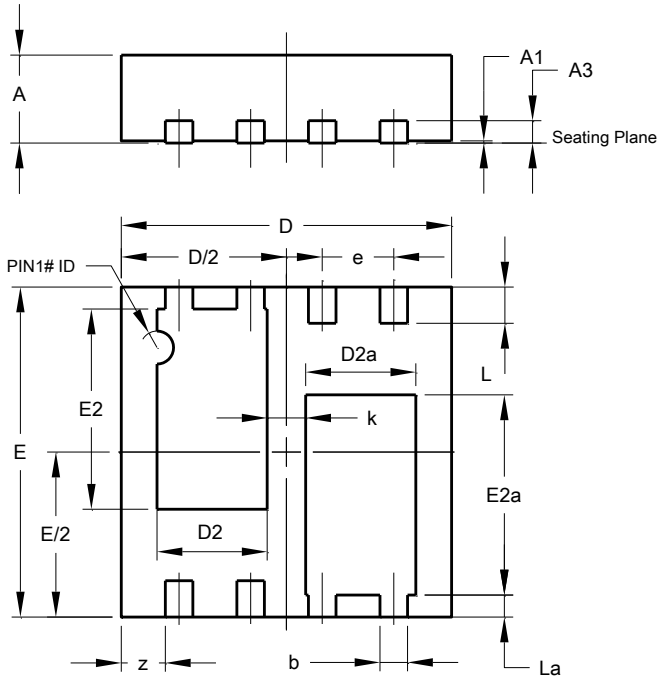


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

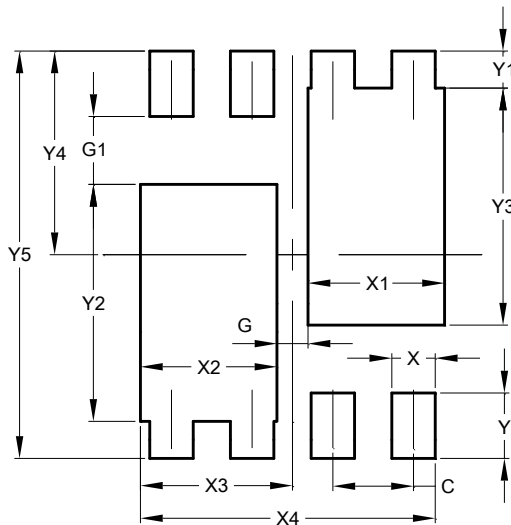
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



V-DFN3030-8 (Type J)			
Dim	Min	Max	Typ
A	0.77	0.83	0.80
A1	0.00	0.05	0.02
A3	0.203 BSC		
b	0.20	0.30	0.25
D	2.95	3.050	3.00
D2	0.90	1.10	1.00
D2a	0.90	1.10	1.00
E	2.95	3.050	3.00
E2	1.72	1.92	1.82
E2a	1.72	1.92	1.82
e	0.65BSC		
L	0.27	0.38	0.33
La	0.15	0.25	0.20
k	0.35 TYP		
z	0.40 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.250
G1	0.550
X	0.350
X1	1.100
X2	1.100
X3	1.225
X4	2.375
Y	0.530
Y1	0.300
Y2	1.920
Y3	1.920
Y4	1.650
Y5	3.300

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